

**REPLACEMENT CLAIMS**

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92. (Amended) A method for etching an oxide layer of a substrate, comprising:  
placing a substrate having an oxide layer formed over said substrate into a  
reactive chamber;

introducing an etching gas into said reactive chamber;

generating a plasma of said etching gas at a first power level and contacting said  
oxide layer of said substrate with said first power level plasma for a first predetermined time;  
and

B1     generating a plasma of said etching gas at a second power level in said reactive  
chamber and contacting said oxide layer of said substrate with said second power level  
plasma for a second predetermined time to etch said oxide layer, wherein said first and  
second power levels are different.

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